AMENDMENTS TO THE CLAIMS:

This listing of claims that follows is provided as a courtesy. No changes have been made since the previous amendment.

1-15. (Cancelled).

16. (Previously Presented) A method of forming a metal gate electrode with multiple work function, the method comprising the steps of:

depositing a dielectric on a substrate;

depositing a first metallic conductor having a first work function over the dielectric;

depositing a conductive hard mask on the first metallic conductor including at least one of a metal containing conductor and a metal silicide;

removing the conductive hard mask from an area for a particular device type using a photoresist mask;

removing the photoresist mask to a remaining portion of the conductive hard mask;

removing the first metallic conductor in the area using the remaining portion of the conductive hard mask to protect the first metallic conductor;

depositing a second metal having a second, different work function in the area;

depositing a silicon-containing conductor over the first and second metals; and

forming the metal gate electrode including the remaining portion of the conductive hard mask.

17. (Original) The method of claim 16, wherein the metal silicide includes one of tungsten silicide (WSi), titanium silicide ($TiSi_x$), tantalum silicide ($TaSi_x$), nickel silicide (NiSi), cobalt silicide ($CoSi_x$), and the metal containing conductor includes one of tantalum nitride (TaN), tantalum silicon nitride (TaSiN).

18. (Original) The method of claim 16, wherein the conductive hard mask has a thickness of no less than 10 Å and no greater than 500 Å.

19. (Original) The method of claim 18, wherein the conductive hard mask has a thickness of no less than 20 Å and no greater than 250 Å.

20. (Original) The method of claim 16, wherein the conductive hard mask removing step includes conducting one of a wet etch and a reactive ion etch.